# **XP06215**

### Silicon NPN epitaxial planar type

### For digital circuits

#### Features

- Two elements incorporated into one package (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

#### Basic Part Number

• UNR2215  $\times$  2

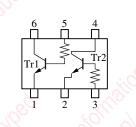
#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Symbol	Rating	Unit	
V <sub>CBO</sub>	50	V	
V <sub>CEO</sub>	50	V	
I <sub>C</sub>	100	mA	
P <sub>T</sub>	150	mW	
Тј	150	°C	
T <sub>stg</sub>	-55 to +150	°C	
	V <sub>CBO</sub> V <sub>CEO</sub> I <sub>C</sub> P <sub>T</sub> T <sub>j</sub>	$\begin{array}{c c} V_{CBO} & 50 \\ \hline V_{CEO} & 50 \\ \hline I_C & 100 \\ \hline P_T & 150 \\ \hline T_j & 150 \\ \hline \end{array}$	

### Package

- Code SMini6-G1
- Pin Name
  - 1: Emitter (Tr1) 4: Collector (Tr2) 2: Emitter (Tr2) 5: Base (Tr1)
  - 3: Base (Tr2)
- 6: Collector (Tr1)
- Marking Symbol: 8X

Internal Connection



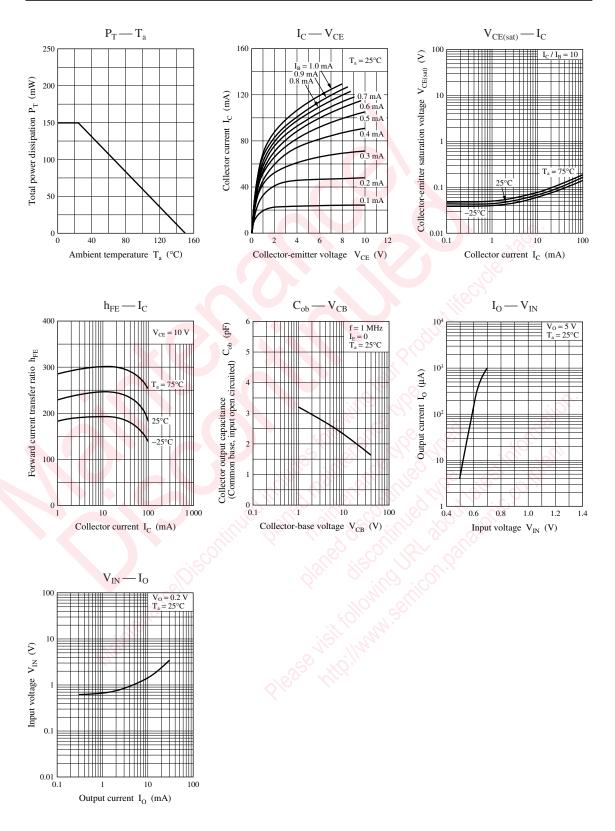
### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 6 V, I_C = 0$			0.01	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$	160		460	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.3 \text{ mA}$			0.25	V
Output voltage high-level	V <sub>OH</sub>	$V_{CC} = 5 \text{ V},  \text{V}_{B} = 0.5  \text{V},  \text{R}_{L} = 1  \text{k}\Omega$	4.9			V
Output voltage low-level	V <sub>OL</sub>	$V_{CC} = 5 \text{ V},  V_{B} = 2.5 \text{ V},  R_{L} = 1  k\Omega$			0.2	V
Input resistance	R <sub>1</sub>		-30%	10	+30%	kΩ
Transition frequency	f <sub>T</sub>	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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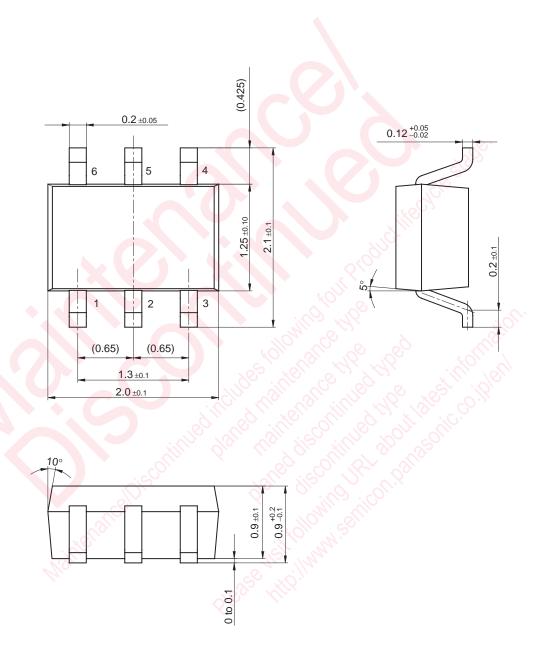




## Panasonic

## SMini6-G1

Unit: mm



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